A multi-layered, thin-film, digital memory having associative recall. There is a first memory matrix and a second memory matrix. Each memory matrix comprises, a first layer comprising a plurality of electrically separated row conductors; a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from the row conductors; and, a plurality of resistance elements electrically connected between the row conductors and the column conductors at respective intersections of the row conductors and the column conductors, each resistance element comprising, in series, a first resistor of sufficiently high ohmage to conduct a sensible element current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross and a second resistor of sufficiently high ohmage to conduct no sensible current therethrough when a low voltage as employed in thin-film applications is applied thereacross, the second resistor having the quality of breaking down to create a short therethrough upon the application of a breakdown level voltage across the first and second resistors.

19 Claims, 4 Drawing Sheets
HIGH DENSITY ASSOCIATIVE MEMORY

ORIGIN OF THE INVENTION

The invention described herein was made in the performance of work under a NASA contract, and is subject to the provisions of Public Law 96-517 (35 USC 202) in which the Contractor has elected to retain title.

BACKGROUND OF THE INVENTION

The present invention relates to mass memory for computers having associative recall capability and, more particularly, to a multi-layered, thin-film, digital memory having associative recall comprising, a first memory matrix and a second memory matrix, each memory matrix comprising, (1) a first layer comprising a plurality of electrically separated row conductors; (2) a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from the row conductors; and, (3) a plurality of resistance elements electrically connected between the row conductors and the column conductors at respective intersections of the row conductors and the column conductors, each resistance element comprising, in series, a first resistor of sufficiently high ohmage to conduct a sensible current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross and a second resistor of sufficiently high ohmage to conduct no sensible current therethrough when a low voltage as employed in thin-film applications is applied thereacross, the second resistor having the quality of breaking down to create a short therethrough upon the application of a breakdown level voltage across the first and second resistors; a plurality of bi-stable sense amplifier means each having an input connected to a respective one of the column conductors of the second matrix for indicating at an output thereof when a current flow is detected at the input in the one of the column conductors of the second matrix connected thereto; a plurality of current summing amplifier means each having an output connected to a respective one of the row conductors of the second matrix for applying a voltage to the one of the row conductors of the second matrix connected thereto when the current into a second input thereof exceeds the current into a first input thereof, the row conductors of the first matrix being electrically connected to respective ones of the second inputs; a plurality of bi-stable read driver means each having an output connected to a respective one of the column conductors of the first matrix for outputting a voltage when an input thereof has a binary "1" prompt value applied thereto and for not outputting a voltage when the input thereof has a binary "0" prompt value applied thereto; and, ramped read driver means having an output connected to the first inputs of the current summing amplifier means for producing a downward ramp at the output thereof starting at a value higher than the maximum possible value at the second inputs and decreasing until one of the current summing amplifier means has its second input value higher than the output of the ramped read driver means and applies a voltage to the one of the row conductors of the second matrix connected thereto.

Computer memory has gone through much evolution in the short time that digital computers have been generally available. The original computers had only one memory—a rotating drum with a magnetizable surface rotating past a plurality of read and write heads. With the advent of so-called core memory for the "main" memory, there was a functional split between the main memory which was generally small (12-16K words), high priced, and bulky and mass memory that provided storage at a much lower price per word for large masses of data and programs that were only used occasionally. As depicted in FIG. 1, the early core memories comprised a plurality of annular ferrite cores 12 strung on a matrix of row and column wires 14 and 16. The core memories offered random access to each word stored therein (i.e. equal access time) while the mass storage devices (such as the drum memories) had inherent access times caused by rotational delays of the drum with respect to the read heads. Later developed rotational mass storage devices such as disk drives reduced the size of the device; but, did nothing to overcome the rotational delays and, in fact, added additional delays in the form of arm movement radially in an out to position the heads on the disk.

More exotic developments in the memory art have provided main memory without the old ferrite cores and the ability to offer large memory matrices such as that indicated as 18 in FIG. 2 with no moving parts. The memory matrix 18 has row conductors 20 on one layer and column conductors 22 on an adjacent layer. The interconnections between the conductors, 20, 22 are accomplished with transistors, or the like, which can be set to a "1" or "0" state (i.e. bi-stable or binary in nature) and then be read at a later time. Main memory is now routinely offered in mega-bytes with mass memory still limited to the use of rotational devices with their inherent limitations (imposed for a great part by a 3,000 rpm rotational maximum) or the use of main memory technology.

Space applications for computers have imposed additional constraints on memory technology. Many devices and technologies react unfavorably to the radiation encountered in space. At present, there is no memory available which offers large storage capacity in a small space employing thin film technology in a manner which has no moving parts and is radiation resistant.

STATEMENT OF THE INVENTION

This invention provides a mass memory for digital computers which has the capability of large storage capacity in a small space and employing thin film technology in a manner which has no moving parts and is radiation resistant. More particularly, the invention is directed to the method and associated apparatus for constructing, writing to, and reading from a multi-layered, thin-film, radiation-resistant, digital memory with associative recall capability comprising the steps of: constructing a first memory matrix and a second memory matrix wherein the construction of each matrix comprises the steps of, forming a first layer comprising a plurality of electrically separated row conductors; forming a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from the row conductors; and, forming a plurality of resistance elements electrically connected between the row conductors and the column conductors at respective intersections of the row conductors and the column conductors wherein each resistance element comprises, in se-
representing data can be read. Moreover, if the resistance of a "1" intersection is accurately set in the order of one meg-ohm and a "0" intersection is a resistance of several orders of magnitude larger, the difference between a "1" and a "0" will be detectable and the power consumption (and, therefore heat generated) can be made significantly lower than in random access memories.

Turning now to FIG. 4, a memory segment 26 according to the present invention is shown in simplified symbolic form following construction and prior to data being written therein. Each intersection between a row conductor 20 and a column conductor 22 has a connection comprising a resistor 24 in series with a switch 28. The resistors are substantially identical and of about one meg-ohm. As symbolically depicted in FIG. 5, data is written into the memory segment 26 by closing the switches 28 where a "1" is desired, thus connecting the resistor 24 between the row conductor 20 and a column conductor 22 at that intersection.

Turning now to FIG. 6, an actual memory segment 26' according to the present invention is shown in simplified form following construction and prior to data being written therein. Each intersection between a row conductor 20 and a column conductor 22 has a connection comprising a low resistance resistor 24 in series with a high resistance resistor 30. The resistors 24 are substantially identical and of about one meg-ohm. The resistors 30 are several orders of magnitude larger. As depicted in FIG. 7, data is written into the memory segment 26' by connecting write drivers 32 across the intersections where a "1" is desired. Each driver 32 is at one-half the breakdown potential of the high resistance resistor 30 in the path. One driver 32 across a given intersection is negative while the other is positive; thus, the potential across the high resistance resistor 30 is equal to the breakdown voltage causing the resistor to breakdown or short, thereby connecting only the resistor 24 between the row conductor 20 and a column conductor 22 at that intersection.

The preferred material for construction of memories according to the present invention at this time is hydrogenated amorphous silicon. An instant advantage of this material is its resistance to being affected by radiation. As mentioned under the Discussion of the Cited References section, the co-pending patent applications listed in the List of Cited References section describe in detail the preferred manner of forming the resistors employed in the memory of the present invention and reference should be made thereto for more details of process which forms no patentable part of this invention. The preferred structure of each intersection of this invention subsequent to formation is depicted in FIGS. 8 and 9. The row conductor 20 on one layer is connected to the column conductor on another layer by a formed resistance path comprising the resistor 24 on the same layer as one conductor 20, 22 and an overlapping spaced breakdown point separated by a breakdown layer 34 comprising the resistor 30. A memory structure constructed thus is capable of storing up to 10⁹ bits per cm². Having thus described the preferred manner of constructing and writing into the memory of the present invention, the preferred architecture therefor to achieve additional benefits will now be described in detail.

As those skilled in the art will appreciate from the description heretofore, the memory of the present invention is, of course, a read only memory or ROM; that is, once the data has been written, it cannot be changed.
FIG. 10. The column conductors 22 of the input matrix 42 are connected to the outputs of respective ones of a plurality of drivers 50 which can be loaded with (i.e., be changeably set to output) binary associative prompt values. Finally, the row conductors 20 of the output matrix 44 are connected as individual inputs to an OR gate 52 having an output connected to the ramped reader driver 48. The associative operation of these components will now be described.

The ramped reader driver 48 outputs a declining ramp voltage to all the summing amplifiers 46. The voltage is chosen to start high enough to assure that all the amplifiers 46 are forced OFF. A binary prompt value is first loaded into the drivers 50. For example, let us assume that it is desired to find the contents of the word in the output matrix 44 which is closest to binary 011000. Note that this exact binary value does not exist in the output matrix 44. The associative nature of the present invention is such that it will find the word closest to the prompt value. Promoted by the value 011000, the second and third drivers 50 will apply an output to their respective column conductors 22 while the remaining drivers 50 will not produce an output. As indicated by the dashed arrows, the output from the second driver 50 has two "low" resistance connections for current flow to row conductors 20, i.e. at words #2 and #4. Similarly, the output from the third driver 50 has two "low" resistance connections to row conductors 20, i.e. at words #1 and #2. As a result, the summing amplifier 46 for word #1 has a current input level of one, indicating one "right" bit in the word relative to the prompt value. The summing amplifier 46 for word #2 has an input level of two (i.e. there are two current paths inputting to it), indicating two "right" bits in the word relative to the prompt value while the amplifier 46 for word #4, like the amplifier 46 for word #1, has a current input value of one. Under those conditions, the ramp out of the ramped read driver 48 is decreased until one of the current summing amplifiers 46 has its positive input exceed its negative input. In this case, the word #2 amplifier with a positive value associated with two current paths will be the first to exceed the decreasing ramp voltage (since it has the most "right" bits vis-a-vis the prompt value). As soon as the word #2 amplifier outputs to its associated row conductor 20 that output is sensed at the OR gate 52 causing it to output a RAMP STOP command to the ramped read driver 48. Thus, the contents of word #2, and only word #2, appears at the outputs 38 of the sense amplifiers 36, as is proper. The same operation would, of course, take place if the prompt value was an exact match to a word in the input matrix 42 or if the values in the input matrix 42 were indices, or what have you, instead of being a duplicate of the contents of the output matrix 44 as in the example.

Thus, it can be seen that the memory of the present invention provides a multitude of advantages over the prior art including resistance to radiation effects, high density in small volume, simple read technology, and associative recall, including recall of the closest to a prompt value.

We claim:

1. A multi-layered, thin-film, digital memory comprising:
   (a) a first layer comprising a plurality of electrically separated row conductors;
   (b) a second layer comprising a plurality of electrically separated column conductors intersect electrically separated from said row conductors; and,
   (c) a plurality of resistance elements electrically connected between said row conductors and said column conductors at respective intersections of said row conductors and said column conductors, each resistance element comprising, in series, a first resistor of sufficiently high ohmage to conduct a sensible current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross and a second resistor of sufficiently high ohmage to conduct no sensible current therethrough when a low voltage as employed in thin-film applications is applied thereacross, said second resistor having the quality of breaking down to create a short therethrough upon the application of a breakdown level voltage across said second resistor.

2. The thin-film digital memory of claim 1 wherein:
   said second resistors are each formed of a resistive third layer disposed between overlapped conductor portions on said first and second layers.

3. The thin-film digital memory of claim 1 and additionally comprising:
   a plurality of bistable sense amplifier means each having an input connected to a respective one of said column conductors for indicating at an output thereof when a current flow is detected at said input in the one of said column conductors connected thereto.

4. A multi-layered, thin-film, digital memory having associative recall comprising:
   (a) a first memory matrix and a second memory matrix, each said memory matrix comprising,
      (a1) a first layer comprising a plurality of electrically separated row conductors;
      (a2) a second layer comprising a plurality of electrically separated row conductors intersecting but electrically separated from said row conductors; and,
      (a3) a plurality of resistance elements electrically connected between said row conductors and said column conductors at respective intersections of said row conductors and said column conductors, each resistance element comprising, in series, a first resistor of sufficiently high ohmage to conduct a sensible current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross and a second resistor of sufficiently high ohmage to conduct no sensible current therethrough when a low voltage as employed in thin-film applications is applied thereacross, said second resistor having the quality of breaking down to create a short therethrough upon the application of a breakdown level voltage across said second resistor; and,
   (b) a plurality of bistable sense amplifier means each having an input connected to a respective one of said column conductors of said second matrix for indicating at an output thereof when a current flow is detected at said input in the one of said column conductors of said second matrix connected thereto;
(c) a plurality of current summing amplifier means each having an output connected to a respective one of said row conductors of said second matrix for applying a voltage to the one of said row conductors of said second matrix connected thereto when the current into a second input thereof exceeds the current into a first input thereof, said row conductors of said first matrix being electrically connected to respective ones of said second inputs;
(d) a plurality of bi-stable read driver means each having an output connected to a respective one of said column conductors of said first matrix for outputting a voltage when an input thereof has a binary "1" prompt value applied thereto and for not outputting a voltage when said input thereof has a binary "0" prompt value applied thereto; and,
(e) ramped read driver means having an output connected to said first inputs of said current summing amplifier means for producing a downward ramp at said output thereof starting at a value higher than the maximum possible value at said second inputs and decreasing until one of said current summing amplifier means has its said second input value higher than the output of said ramped read driver means and applies a said voltage to the one of said row conductors of said second matrix connected thereto.
5. The multi-layered, thin-film, digital memory having associative recall of claim 4 wherein:
(a) second resistors are each formed of a resistive third layer disposed between overlapped conductor portions on said first and second layers.
6. The multi-layered, thin-film, digital memory having associative recall of claim 4 and additionally comprising:
(a) forming a first layer comprising a plurality of resistance elements electrically connecting respective ones of said row conductors of said second matrix for outputting a stop ramp command to said ramped read driver means to cause said ramp to stop when said one of said current summing amplifier means has its said second input value higher than the output of said ramped read driver means and applies a said voltage to the one of said row conductors of said second matrix connected thereto;
(b) forming a second layer comprising a plurality of electrically separated column conductors intersecting electrically separated column conductors in series of electrically separated column conductors intersecting but electrically separated from the row conductors connected thereto.
7. The method of forming and writing into a multi-layered, thin-film, read-only, digital memory comprising:
(a) forming a first layer comprising a plurality of electrically separated row conductors;
(b) forming a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from the row conductors.
(c) forming a plurality of resistance elements electrically connected between the row conductors and the column conductors at respective intersections of the row conductors and the column conductors wherein each resistance element comprises, in series, a first resistor of sufficiently high ohmage to conduct a sensible current therethrough but electrically separated from the row conductors; and,
(d) writing data into the memory by applying a voltage across each second resistor wherein there is to be a binary "1" sufficiently high so as to break down that second resistor and create a short therethrough.
8. The method of claim 7 and additionally comprising the steps for reading the contents of the memory of:
(a) connecting the inputs of a plurality of bi-stable sense amplifiers to respective ones of the column conductors to indicate at outputs thereof when a current flow is detected at the input in the one of the column conductors connected thereto;
(b) applying a voltage to the row conductor associated with a word of the memory to be read; and,
(c) reading the contents of the word at the outputs of the sense amplifiers.
9. The method of constructing, writing to, and reading from a multi-layered, thin-film, digital memory with associative recall comprising the steps of:
(a) constructing a first memory matrix and a second memory matrix, the construction of each matrix comprising the steps of:
(a1) forming a first layer comprising a plurality of electrically separated row conductors;
(a2) forming a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from the row conductors; and,
(a3) forming a plurality of resistance elements electrically connected between the row conductors and the column conductors at respective intersections of the row conductors and the column conductors wherein each resistance element comprises, in series, a first resistor of sufficiently high ohmage to conduct a sensible current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross and a second resistor of sufficiently high ohmage to conduct no sensible current therethrough when a low voltage as employed in thin-film applications is applied thereacross;
(b) writing output data into the second memory matrix by applying a voltage across each second resistor thereof wherein there is to be a binary "1" sufficiently high so as to break down that second resistor and create a short therethrough;
(c) writing associative input data into the first memory matrix by applying a voltage across each second resistor thereof wherein there is to be a binary "1" sufficiently high so as to break down that second resistor and create a short therethrough;
(d) connecting the inputs of a plurality of bi-stable sense amplifiers to respective ones of the column conductors of the second matrix to indicate at outputs thereof when a current flow is detected at the input in the one of the column conductors of the second matrix connected thereto;
(e) connecting the outputs of a plurality of current summing amplifiers to respective ones of the row conductors of the second matrix to apply a voltage to the one of the row conductors of the second matrix connected thereto when the current into a second input thereof exceeds the current into a first input thereof;
(f) electrically connecting respective ones of the row conductors of the first matrix to the second inputs;
11. A multi-layered, thin-film, digital memory comprising:
(a) a first layer comprising a plurality of electrically separated row conductors;
(b) a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from said row conductors; and,
(c) a plurality of resistance element means electrically connected between said row conductors and said column conductors for creating a first resistor of sufficiently high ohm-age to conduct a sensible current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross at locations where there is to be a second binary value.

12. The thin-film digital memory of claim 11 wherein:
(a) said resistance element means each comprises a said first resistor and a said second resistor in series, said 60 second resistor having a sensitivity of breaking down upon the application of a voltage across said first resistor and said second resistor.

14. The thin-film digital memory of claim 11 and additionally comprising:
(a) a plurality of bi-stable sense amplifier means each having an input connected to a respective one of said column conductors for indicating at an output thereof when a current flow is detected at said input in the one of said column conductors connected thereto.
(b) a plurality of bi-stable read driver means each having an input connected to a respective one of said column conductors for indicating at an output thereof when a current flow is detected at said input in the one of said column conductors connected thereto.

15. A multi-layered, thin-film, digital memory having associative recall comprising:
(a) a first memory matrix and a second memory matrix, each said memory matrix comprising,
(a1) a first layer comprising a plurality of electrically separated row conductors;
(a2) a second layer comprising a plurality of electrically separated column conductors intersecting but electrically separated from said row conductors; and,
(a3) a plurality of resistance element means electrically connected between said row conductors and said column conductors at respective intersections of said row conductors and said column conductors for creating a first resistor of sufficiently high ohmage to conduct a sensible current therethrough with virtually no heat-generating power consumption when a low voltage as employed in thin-film applications is applied thereacross at locations where there is to be a second binary value;
(b) a plurality of bi-stable sense amplifier means each having an input connected to a respective one of said column conductors of said second matrix for indicating at an output thereof when a current flow is detected at said input in the one of said column conductors of said second matrix connected thereto;
(c) a plurality of current summing amplifier means each having an output connected to a respective one of said row conductors of said second matrix for applying a voltage to the one of said row conductors of said second matrix connected thereto when the current into a second input thereof exceeds the current into a first input thereof, said row conductors of said first matrix being electrically connected to respective ones of said second inputs;
(d) a plurality of bi-stable read driver means each having an output connected to a respective one of said column conductors of said first matrix for outputting a voltage when an input thereof has a binary "1" prompt value applied thereto and for not outputting a voltage when said input thereof has a binary "0" prompt value applied thereto; and,
(e) ramped read driver means having an output connected to said first inputs of said current summing amplifiers for producing a downward ramp at said output thereof starting at a value higher than the maximum possible value at said second inputs and decreasing until one of said current summing amplifier means has its said second input value higher than the output of said ramped read driver means and applies a said voltage to the one of said row conductors of said second matrix connected thereto.
16. The thin-film digital memory of claim 15 wherein: said resistance element means each comprises a said first resistor and a said second resistor in series, said second resistor having the quality of breaking down to create a short therethrough upon the application of a breakdown level voltage across said second resistor.

17. The thin-film digital memory of claim 16 wherein:
(a) said first resistor is of about one meg-ohm resistance; and,
(b) said second resistor is several orders of magnitude greater in resistance than said first resistor.

18. The multi-layered, thin-film, digital memory having associative recall of claim 16 wherein:

19. The multi-layered, thin-film, digital memory having associative recall of claim 15 and additionally comprising:

OR gate means having a plurality of inputs connected to respective ones of said row conductors of said second matrix for outputting a stop ramp command to said ramped read driver means to cause said ramp to stop when said one of said current summing amplifier means has its said second input value higher than the output of said ramped read driver means and applies a said voltage to the one of said row conductors of said second matrix connected thereto.